

<DIODE Modules>

# RM1400HA-24S

HIGH POWER SWITCHING USE  
INSULATED TYPE



single pack

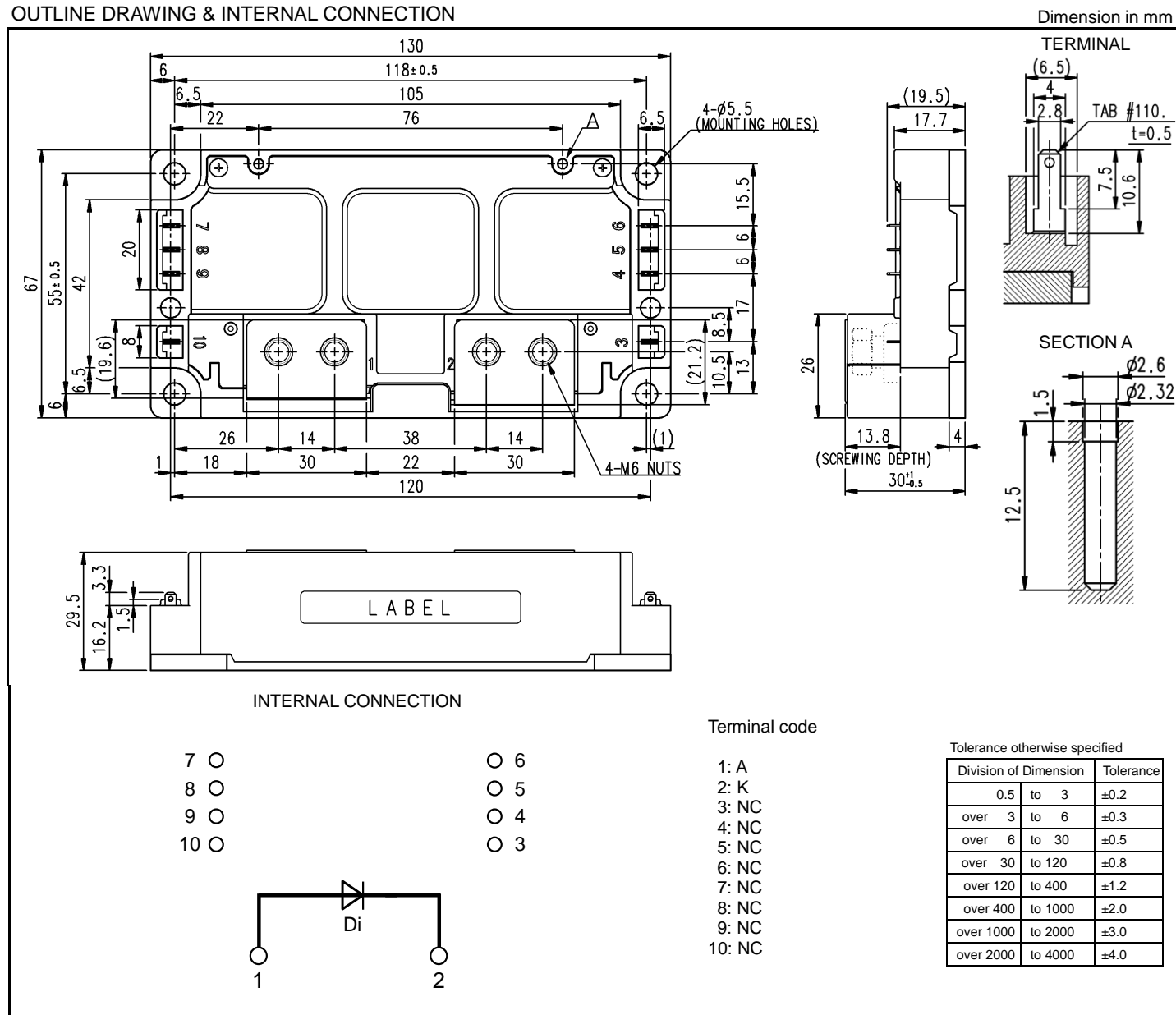
Forward current  $I_{DC}$  ..... **1 4 0 0 A**  
 Repetitive peak reverse voltage  $V_{RRM}$  ..... **1 2 0 0 V**  
 Maximum junction temperature  $T_{vjmax}$  ..... **1 7 5 °C**

- Flat base Type
- Copper base plate
- RoHS Directive compliant
- Recognized under UL1557, File E323585

## APPLICATION

AC Motor Control, Motion/Servo Control, Power supply, Photovoltaic power, Wind power, etc.

## OUTLINE DRAWING & INTERNAL CONNECTION



**RM1400HA-24S**HIGH POWER SWITCHING USE  
INSULATED TYPE**MAXIMUM RATINGS (T<sub>vj</sub>=25 °C, unless otherwise specified)**

Symbol	Item	Conditions	Rating	Unit
V <sub>RRM</sub>	Repetitive peak reverse voltage	-	1200	V
V <sub>RSM</sub>	Non-repetitive peak reverse voltage	-	1200	V
V <sub>R(DC)</sub>	Reverse DC blocking voltage	-	960	V
I <sub>DC</sub>	Forward current	DC (Note1)	1400	A
I <sub>FSM</sub>	Surge non-repetitive forward current	1 cycle of half wave at 60 Hz, peak value, T <sub>vj</sub> =25 °C start, V <sub>RM</sub> =0 V	3526	A
I <sup>2</sup> t	Current square time for fusing	t <sub>w</sub> =8.3 ms, T <sub>vj</sub> =25 °C start, Value for one cycle of surge current	5.16 × 10 <sup>4</sup>	A <sup>2</sup> s
V <sub>isol</sub>	Isolation voltage	Terminals to base plate, RMS, f=60 Hz, AC 1 min	4000	V
T <sub>vjmax</sub>	Maximum junction temperature	Instantaneous event (overload)	175	°C
T <sub>Cmax</sub>	Maximum case temperature	(Note2)	125	
T <sub>vjop</sub>	Operating junction temperature	Continuous operation (under switching)	-40 ~ +150	°C
T <sub>stg</sub>	Storage temperature	-	-40 ~ +125	

**ELECTRICAL CHARACTERISTICS (T<sub>vj</sub>=25 °C, unless otherwise specified)**

ELECTRICAL CHARACTERISTICS (V <sub>A</sub> =25 °C, unless otherwise specified)							
Symbol	Item	Conditions		Limits			Unit
				Min.	Typ.	Max.	
I <sub>RRM</sub>	Reverse current	V <sub>R</sub> =V <sub>RRM</sub> , T <sub>vj</sub> ≒125 °C		-	-	1.0	mA
V <sub>F</sub> (Terminal)	Forward voltage	I <sub>F</sub> =1400 A, V <sub>GE</sub> =15 V, Refer to the figure of test circuit (Note3)	T <sub>vj</sub> =25 °C	-	2.03	2.48	V
			T <sub>vj</sub> =125 °C	-	2.08	-	
			T <sub>vj</sub> =150 °C	-	2.08	-	
V <sub>F</sub> (Chip)		I <sub>F</sub> =1400 A (Note3)	T <sub>vj</sub> =25 °C	-	1.75	2.20	V
			T <sub>vj</sub> =125 °C	-	1.80	-	
			T <sub>vj</sub> =150 °C	-	1.80	-	
t <sub>rr</sub>	Reverse recovery time	V <sub>CC</sub> =600 V, I <sub>F</sub> =1400 A,		-	-	500	ns
Q <sub>rr</sub>	Reverse recovery charge	V <sub>GE</sub> =±15 V, -diF/dt=11kA/μs,		-	150	-	μC
E <sub>rr</sub>	Reverse recovery energy per pulse	Inductive load		-	104	-	mJ
R <sub>AA'+KK'</sub>	Internal lead resistance	Main terminals-chip, T <sub>C</sub> =25 °C (Note2)		-	0.2	-	mΩ

**THERMAL RESISTANCE CHARACTERISTICS**

Symbol	Item	Conditions	Limits			Unit
			Min.	Typ.	Max.	
R <sub>th(j-c)</sub>	Thermal resistance	Junction to case (Note2)	-	-	32	K/kW
R <sub>th(c-s)</sub>	Contact thermal resistance	Case to heat sink, Thermal grease applied (Note2, 4)	-	18	-	K/kW

**MECHANICAL CHARACTERISTICS**

Symbol	Item	Conditions	Limits			Unit
			Min.	Typ.	Max.	
M <sub>t</sub>	Mounting torque	Main terminals M 6 screw	3.5	4.0	4.5	N·m
M <sub>s</sub>	Mounting torque	Mounting to heat sink M 5 screw	2.5	3.0	3.5	N·m
d <sub>s</sub>	Creepage distance	Terminal to terminal	22.0	-	-	mm
		Terminal to base plate	21.9	-	-	
d <sub>a</sub>	Clearance	Terminal to terminal	16.5	-	-	mm
		Terminal to base plate	12.5	-	-	
e <sub>c</sub>	Flatness of base plate	On the centerline X, Y (Note5)	-50	-	+100	μm
m	mass	-	-	490	-	g

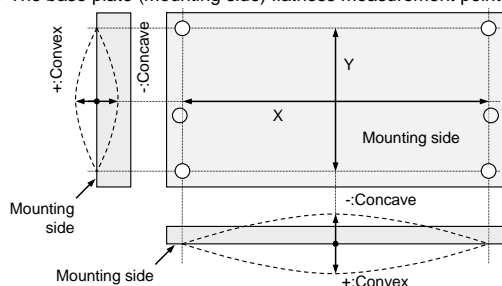
**RM1400HA-24S**

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\*: This product is compliant with the Restriction of the Use of Certain Hazardous Substances in Electrical and Electronic Equipment (RoHS) directive 2011/65/EU.

Note1. Junction temperature ( $T_{vj}$ ) should not exceed  $T_{vjmax}$  rating.

- Case temperature ( $T_c$ ) and heat sink temperature ( $T_s$ ) are defined on the each surface (mounting side) of base plate and heat sink just under the chips. Refer to the figure of chip location.
- Pulse width and repetition rate should be such as to cause negligible temperature rise. Refer to the figure of test circuit.
- Typical value is measured by using thermally conductive grease of  $\lambda=0.9 \text{ W/(m}\cdot\text{K)}/D_{(C-S)}=100 \text{ }\mu\text{m}$ .
- The base plate (mounting side) flatness measurement points (X, Y) are shown in the following figure.



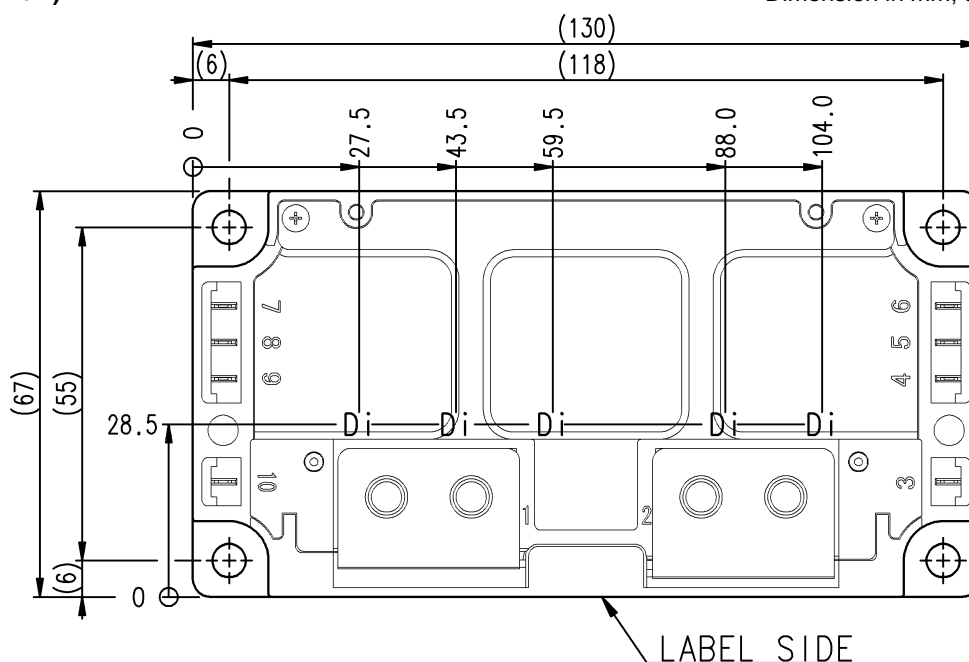
- Use the following screws when mounting the printed circuit board (PCB) on the standoffs.

The length of the screw depends on the PCB thickness ( $t_{1.0}$ ).

Type	Size	Tightening torque	Recommended tightening method
(1) PT®	K25x8	$0.55 \pm 0.055 \text{ N}\cdot\text{m}$	by handwork (equivalent to 30 r/min by mechanical screw driver) ~ 600 r/min (by mechanical screw driver)
(2) PT®	K25x10	$0.85 \pm 0.085 \text{ N}\cdot\text{m}$	
(3) DELTA PT®	25x8	$0.55 \pm 0.055 \text{ N}\cdot\text{m}$	
(4) DELTA PT®	25x10	$0.85 \pm 0.085 \text{ N}\cdot\text{m}$	
(5) B1 tapping screw	$\phi 2.6 \times 10$ or $\phi 2.6 \times 12$	$0.85 \pm 0.085 \text{ N}\cdot\text{m}$	

**CHIP LOCATION (Top view)**

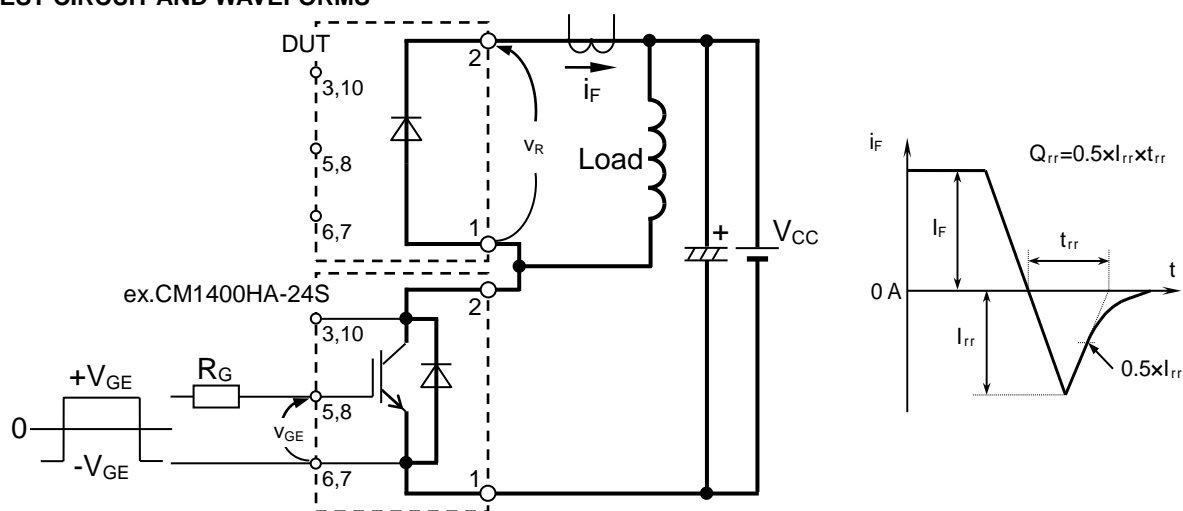
Dimension in mm, tolerance:  $\pm 1 \text{ mm}$



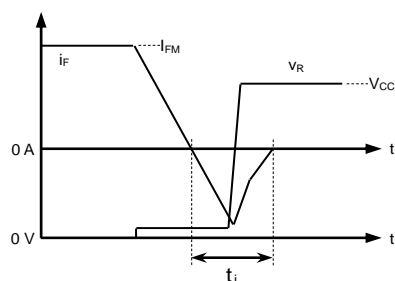
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## TEST CIRCUIT AND WAVEFORMS

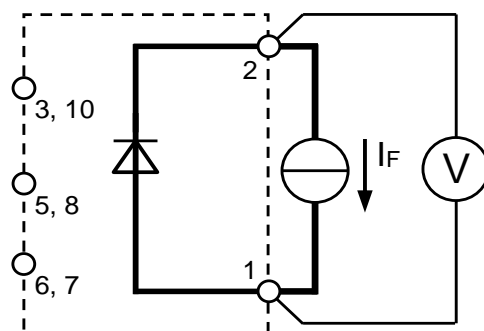


$t_{rr}$ ,  $Q_{rr}$  characteristics test circuit and waveforms



Reverse recovery energy test waveforms (Integral time instruction drawing)

## TEST CIRCUIT

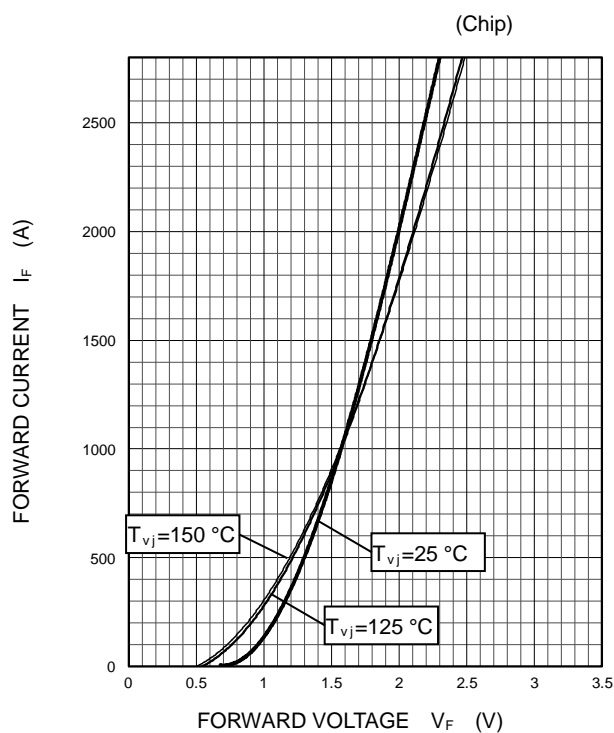


$V_{EC}$  characteristics test circuit

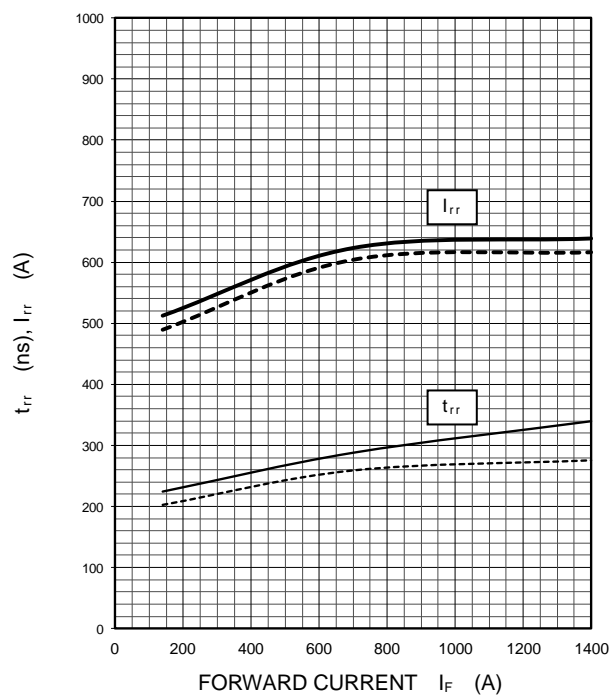
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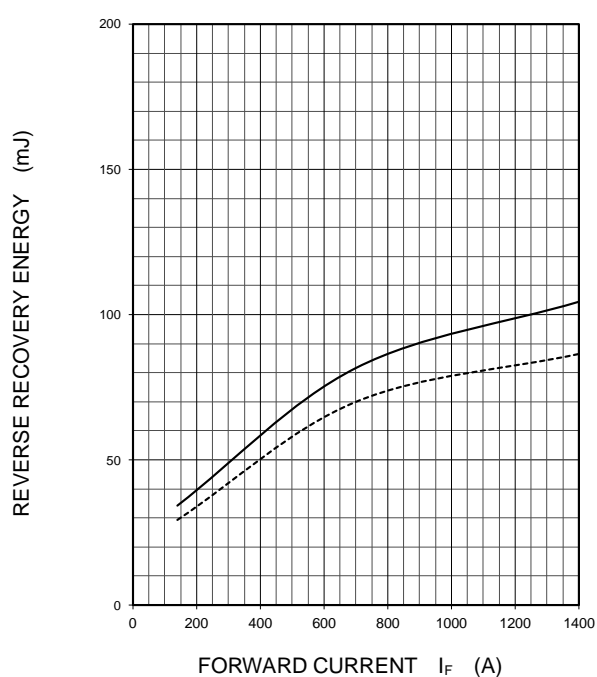
INSULATED TYPE

**PERFORMANCE CURVES****FORWARD CHARACTERISTICS  
(TYPICAL)****REVERSE RECOVERY CHARACTERISTICS  
(TYPICAL)**

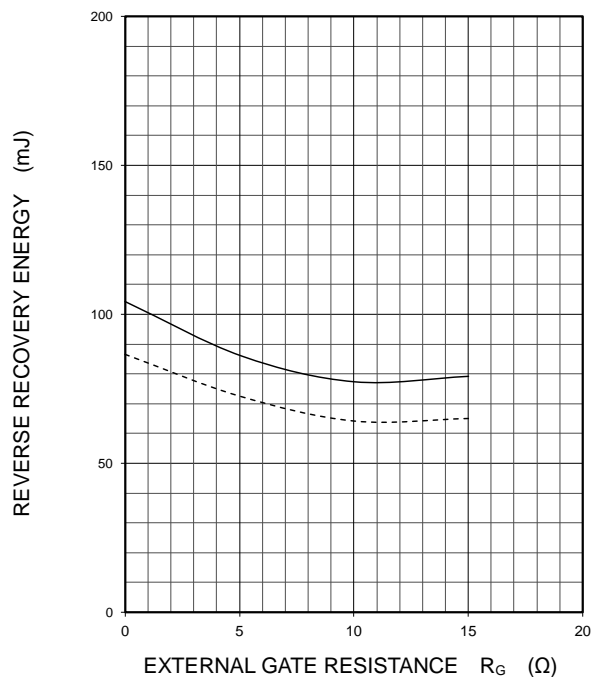
$V_{CC}=600\text{ V}$ ,  $V_{GE}=\pm 15\text{ V}$ ,  $R_G=0\text{ }\Omega$ ,  
INDUCTIVE LOAD by using CM1400HA-24S, PER PULSE  
—:  $T_{vj}=150\text{ }^{\circ}\text{C}$ , - - - -:  $T_{vj}=125\text{ }^{\circ}\text{C}$

**HALF-BRIDGE SWITCHING CHARACTERISTICS  
(TYPICAL)**

$V_{CC}=600\text{ V}$ ,  $V_{GE}=\pm 15\text{ V}$ ,  $R_G=0\text{ }\Omega$ ,  
INDUCTIVE LOAD by using CM1400HA-24S, PER PULSE  
—:  $T_{vj}=150\text{ }^{\circ}\text{C}$ , - - - -:  $T_{vj}=125\text{ }^{\circ}\text{C}$

**HALF-BRIDGE SWITCHING CHARACTERISTICS  
(TYPICAL)**

$V_{CC}=600\text{ V}$ ,  $V_{GE}=\pm 15\text{ V}$ ,  $I_F=1400\text{ A}$ ,  
INDUCTIVE LOAD by using CM1400HA-24S, PER PULSE  
—:  $T_{vj}=150\text{ }^{\circ}\text{C}$ , - - - -:  $T_{vj}=125\text{ }^{\circ}\text{C}$

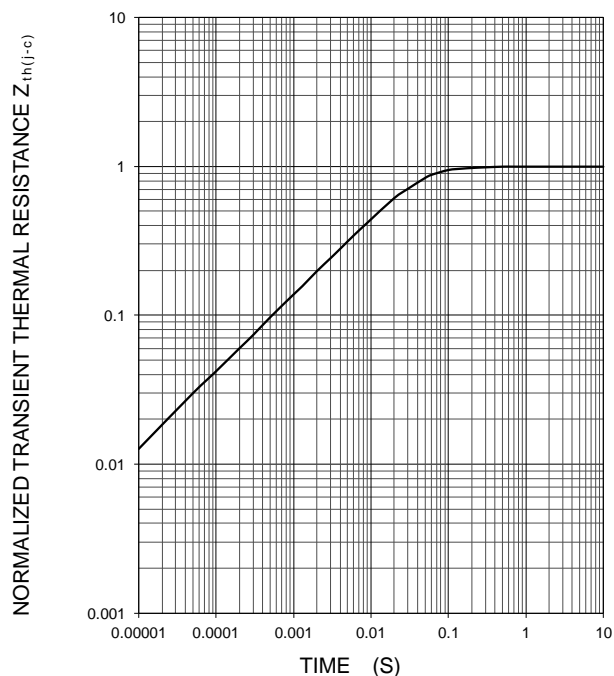


## PERFORMANCE CURVES

### TRANSIENT THERMAL IMPEDANCE CHARACTERISTICS (MAXIMUM)

Single pulse,  $T_C=25\text{ }^{\circ}\text{C}$

$R_{th(j-c)}=32\text{ K/kW}$



Note: The characteristics curves are presented for reference only and not guaranteed by production test, unless otherwise noted.

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